

"SELF-ALIGNED PROCESS USING INDIUM GALLIUM ARSENIDE ETCHING TO FORM  
REENTRY FEATURE IN HETEROJUNCTION BIPOLAR TRANSISTOR"

Scott A. McHugo et al.

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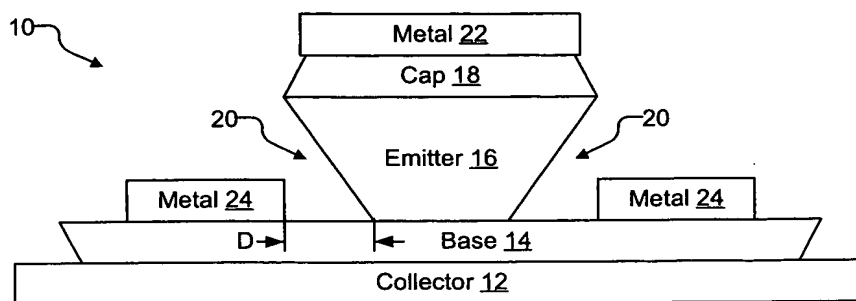


Fig. 1  
(Prior Art)

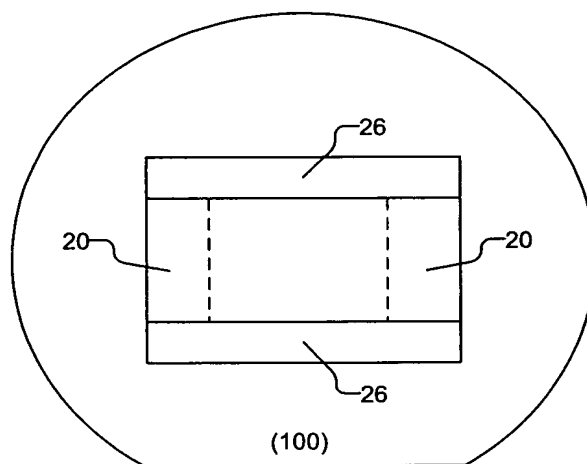


Fig. 2A  
(Prior Art)

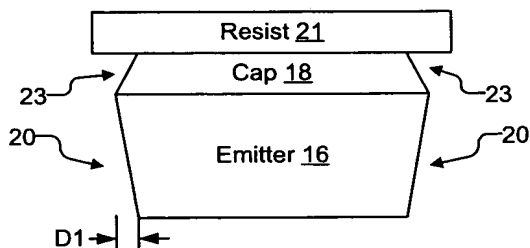


Fig. 2B  
(Prior Art)

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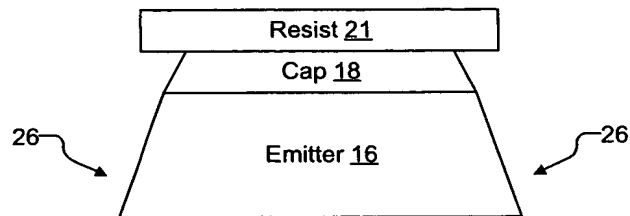


Fig. 2C  
(Prior Art)

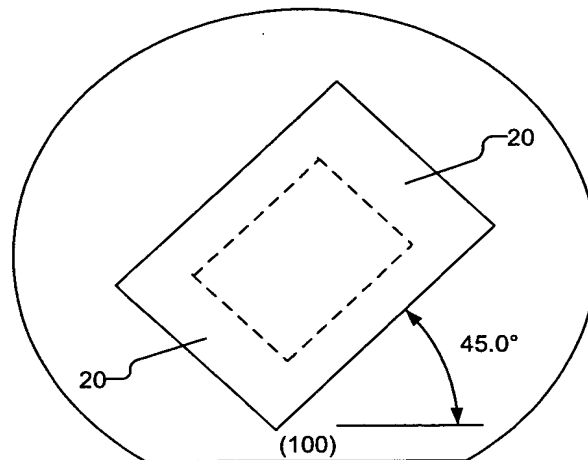


Fig. 3A  
(Prior Art)

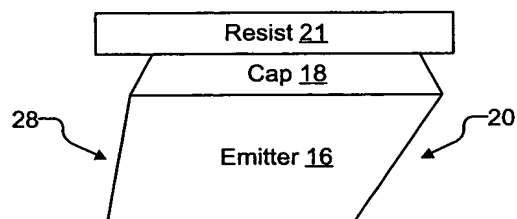


Fig. 3B  
(Prior Art)

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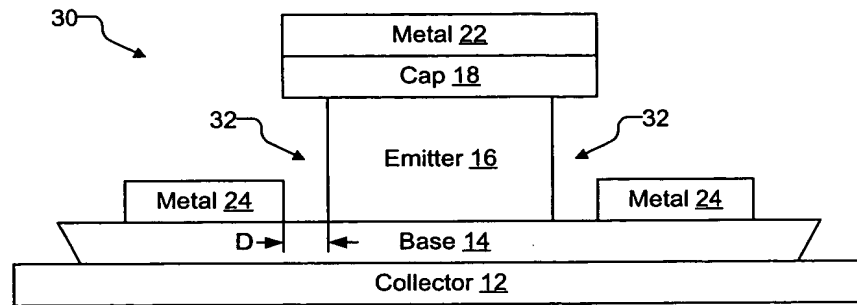


Fig. 4  
(Prior Art)

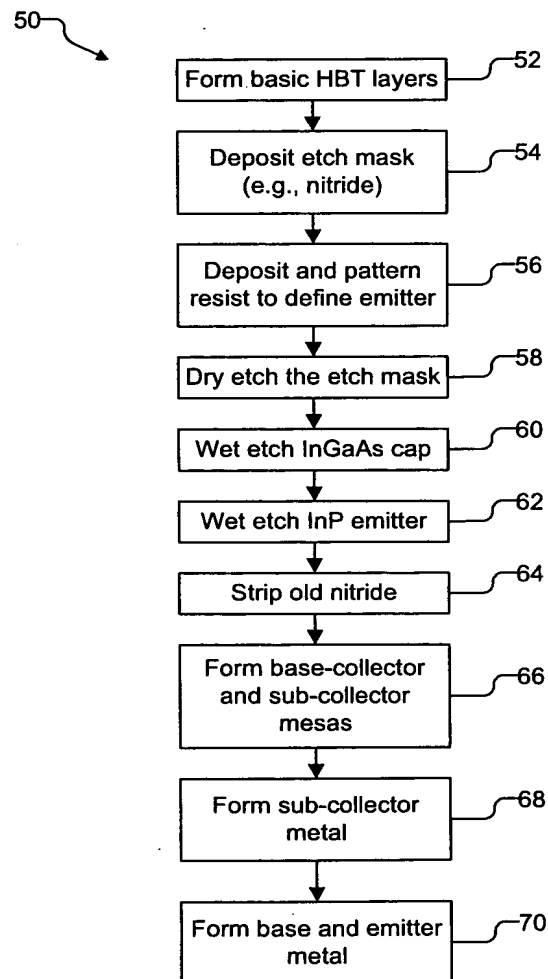


Fig. 5

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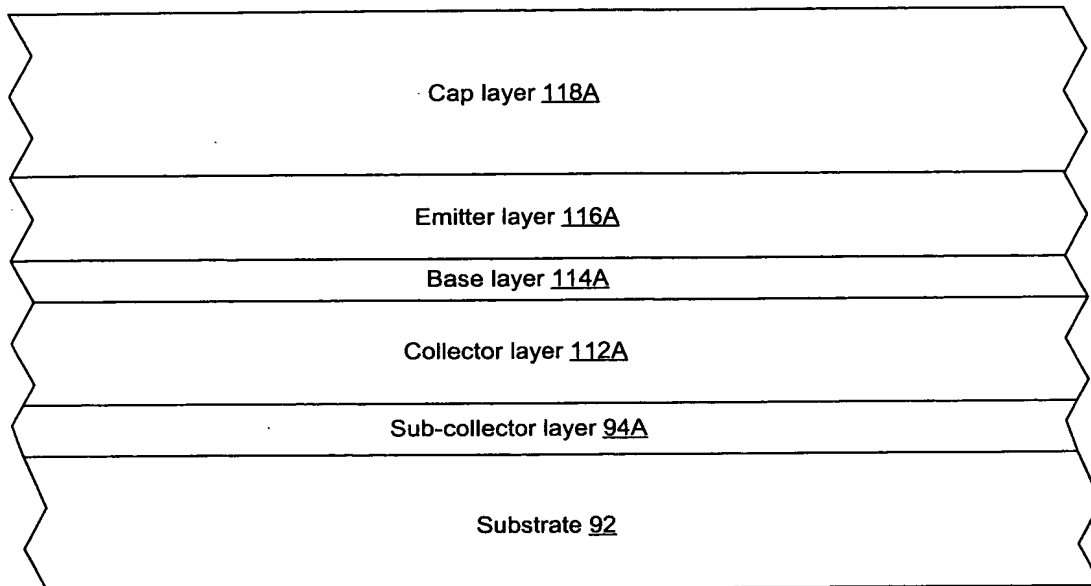


Fig. 6A

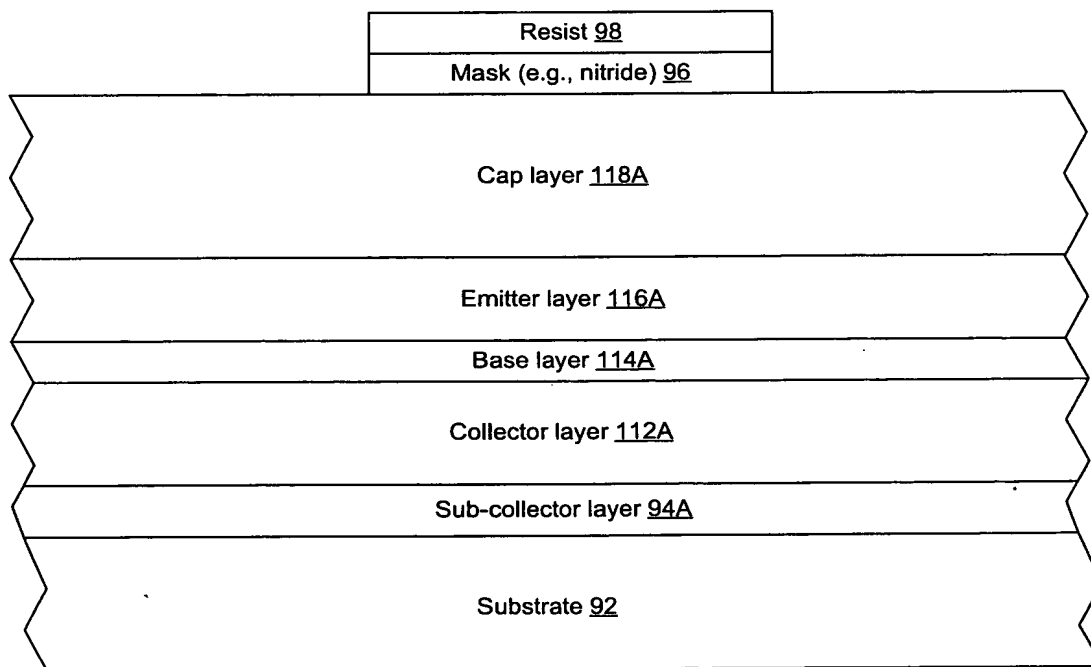


Fig. 6B

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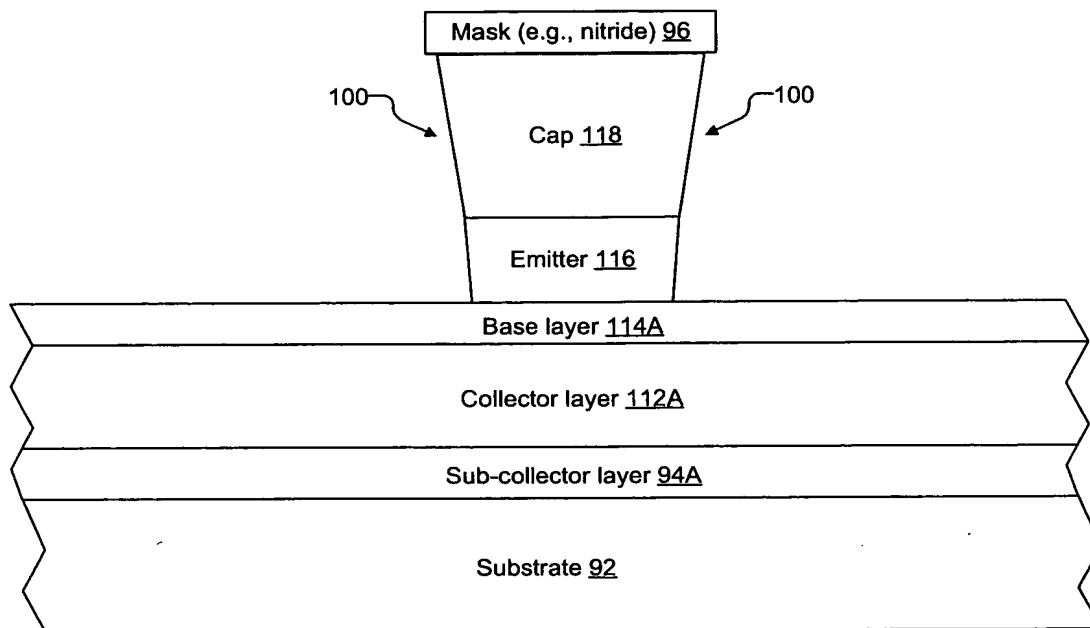


Fig. 6C

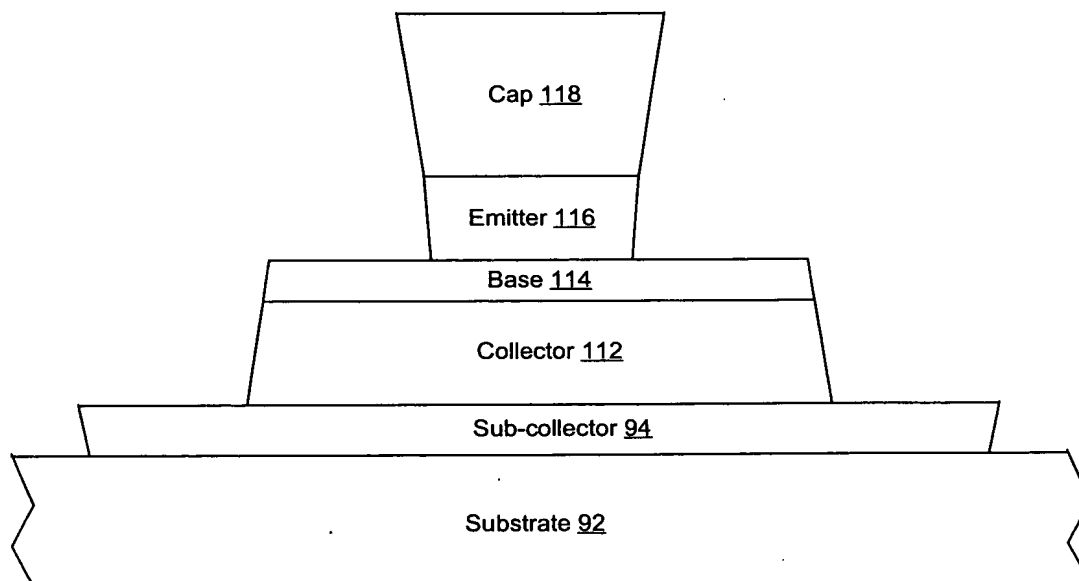


Fig. 6D

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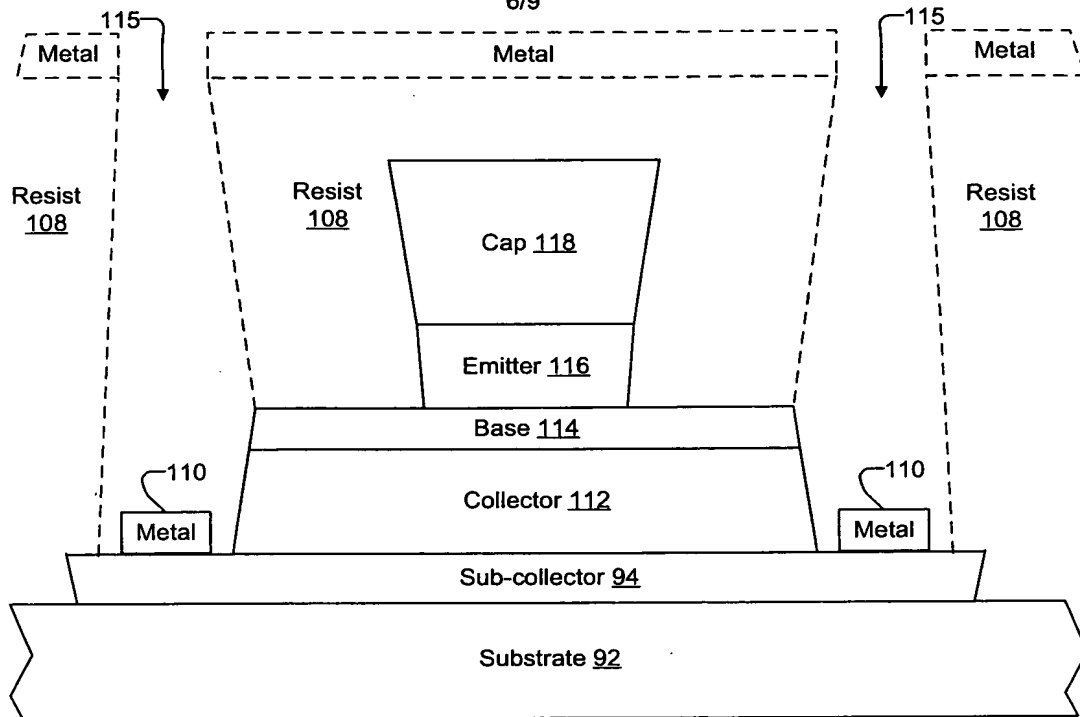


Fig. 6E

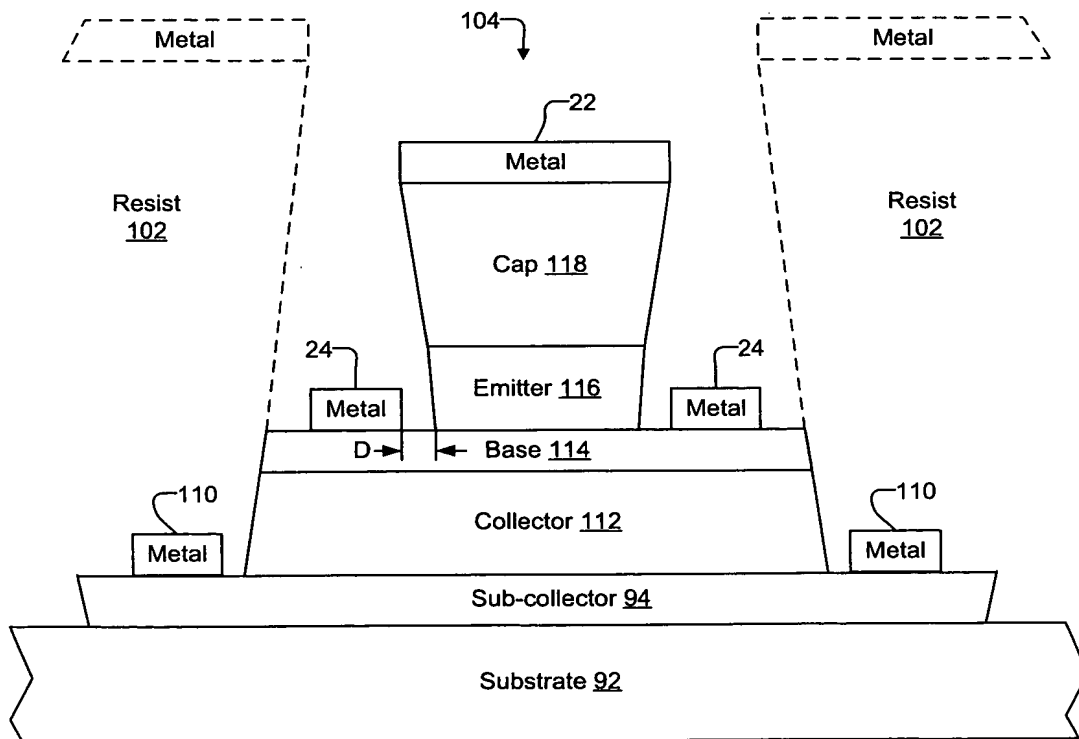


Fig. 6F

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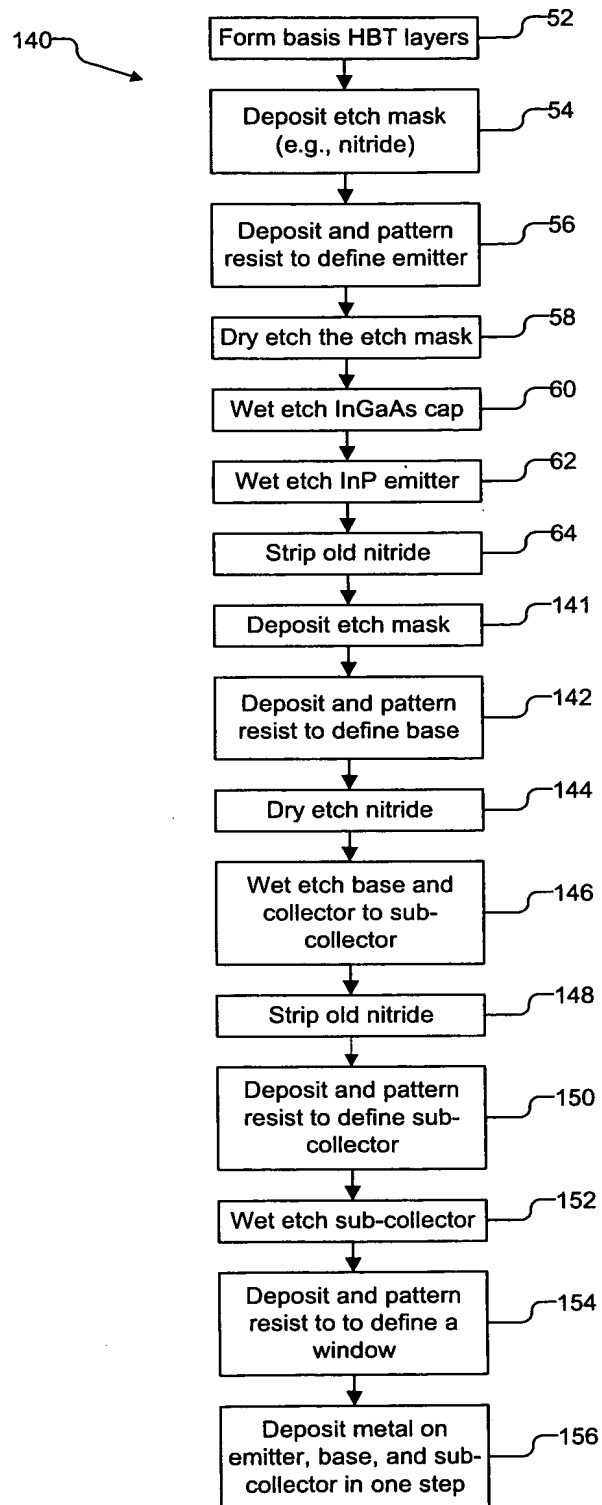


Fig. 7

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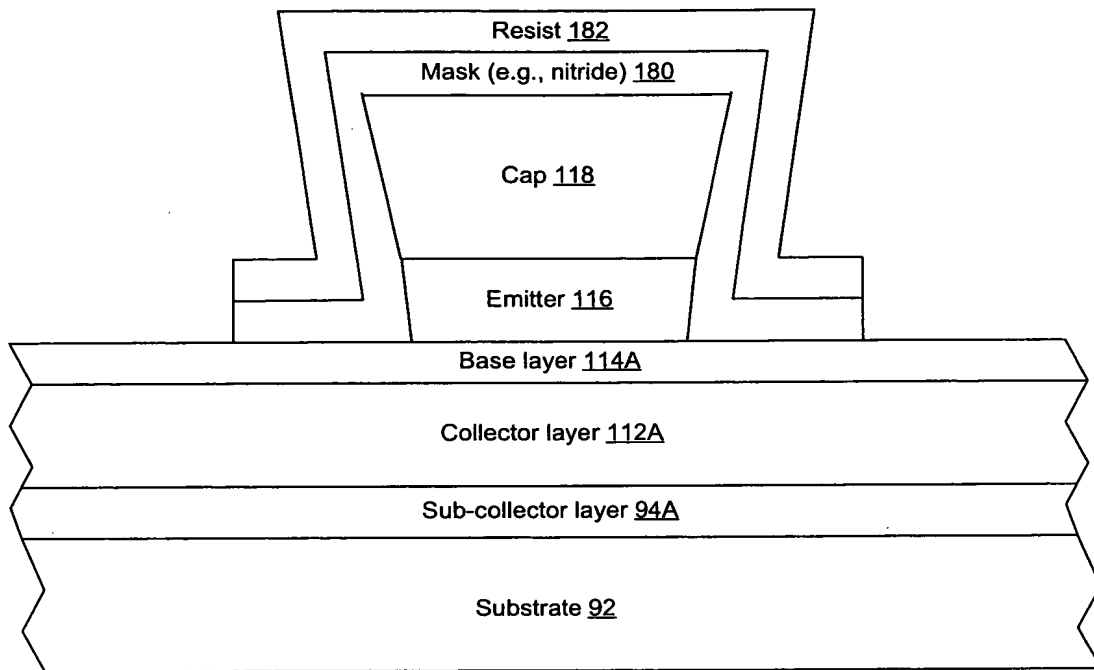


Fig. 8A

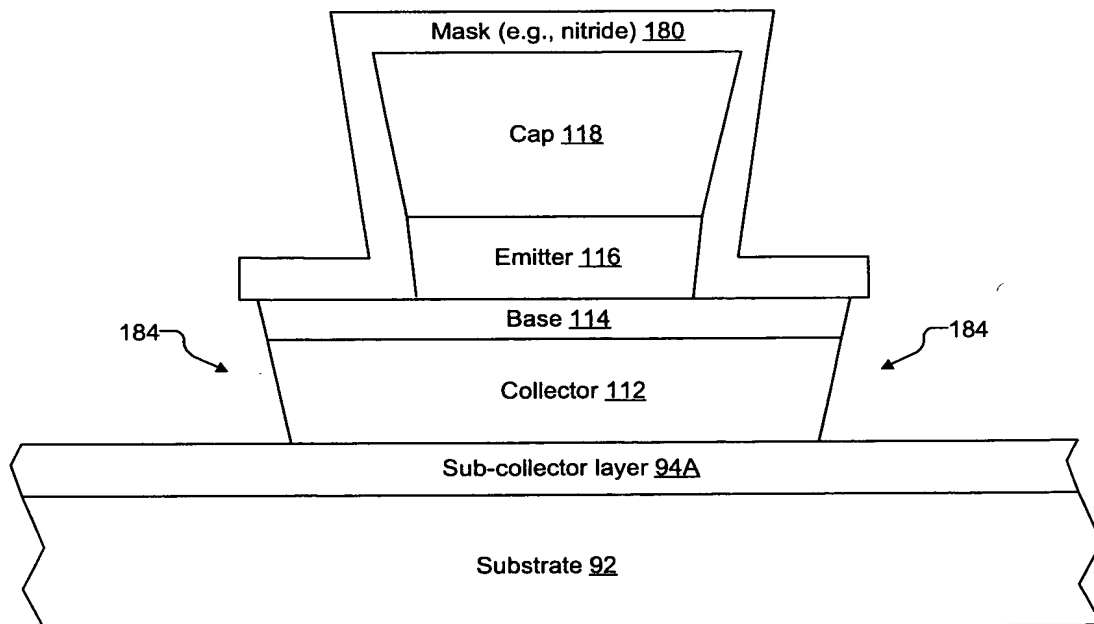


Fig. 8B



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